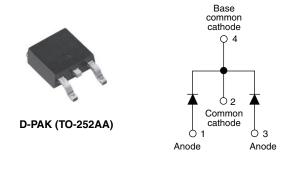
# VS-MURD620CTPbF

Vishay Semiconductors

# Ultrafast Rectifier, 2 x 3 A FRED Pt®



PRODUCT SUMMARY						
Package	D-PAK (TO-252AA)					
I <sub>F(AV)</sub>	2 x 3 A					
V <sub>R</sub>	200 V					
V <sub>F</sub> at I <sub>F</sub>	1.0 V					
t <sub>rr</sub> typ.	See Recovery table					
T <sub>J</sub> max.	175 °C					
Diode variation	Common cathode					

#### FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260  $^\circ\mathrm{C}$

#### **DESCRIPTION/APPLICATIONS**

VS-MURD620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V			
Average rectified forward current per device	I <sub>F(AV)</sub>	Total device, rated $V_R$ , $T_C = 146 \ ^\circ C$	6				
Non-repetitive peak surge current	I <sub>FSM</sub>		50	А			
Peak repetitive forward current per diode	I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, $T_{C}$ = 146 °C	6				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-			
		I <sub>F</sub> = 3 A	-	-	1.0			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	-	0.96	V		
		I <sub>F</sub> = 6 A	-	-	1.2			
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 125 °C	-	-	1.13			
Devenes la slus es sument		V <sub>R</sub> = V <sub>R</sub> rated	-	-	5			
Reverse leakage current	I <sub>R</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	12	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body - 8.0 -				nH		

For technical questions within your region, please contact one of the following: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u>

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## VS-MURD620CTPbF

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# Ultrafast Rectifier, 2 x 3 A FRED Pt<sup>®</sup>



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	-	-	35			
Reverse recovery time t <sub>rr</sub>	+	$I_F = 0.5 \text{ A}, I_R = 1.0$	-	-	25	20		
	۲r	$T_J = 25 \ ^\circ C$		-	19	-	ns	
		T <sub>J</sub> = 125 °C		-	26	-		
Dook roooven ourrent		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 3 A dI <sub>F</sub> /dt = 200 A/μs	-	3.1	-	А	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 160 \text{ V}$	-	4.6	-	A	
	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	]	-	30	-	nC	
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	60	-	110	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C		
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	9.0			
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	80	°C/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	-	-			
Waight			-	0.3	-	g		
Weight			-	0.01	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style D-PAK	MURD620CT					



100

10

1

0.1

0

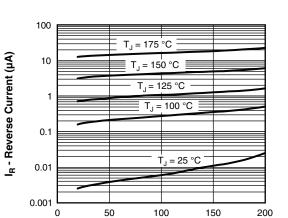
0.2 0.4 0.6 0.8

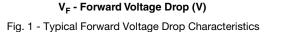
I<sub>F</sub> - Instantaneous Forward Current (A)

### VS-MURD620CTPbF

Ultrafast Rectifier, 2 x 3 A FRED Pt<sup>®</sup>

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T<sub>J</sub> = 175 °C

1.4

1.6

T<sub>J</sub> = 150 °C

T\_J = 25 °C

1.0 1.2



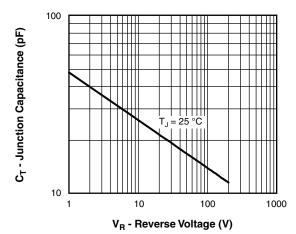


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

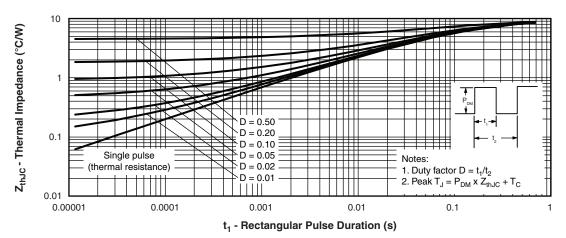


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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Ultrafast Rectifier, 2 x 3 A FRED Pt<sup>®</sup>



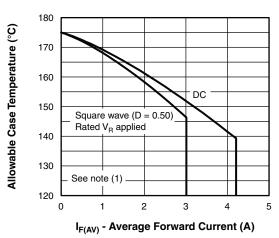


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

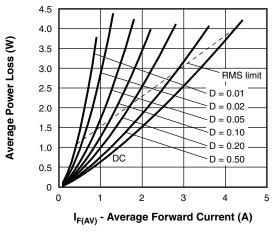


Fig. 6 - Forward Power Loss Characteristics

#### Note

 $^{(1)} \mbox{ Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{th,JC}; \\ Pd = \mbox{ Forward power loss = } I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6); \\ Pd_{REV} = \ Inverse \ power \ loss = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ at \ V_{R1} = \ Rated \ V_R$ 

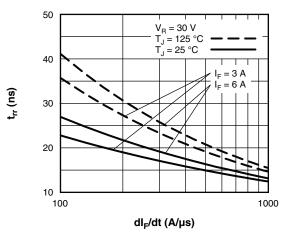


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

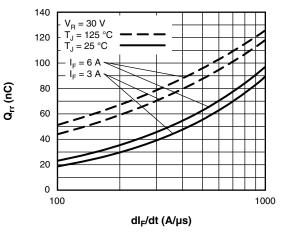


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



# Ultrafast Rectifier, 2 x 3 A FRED $Pt^{\circledast}$

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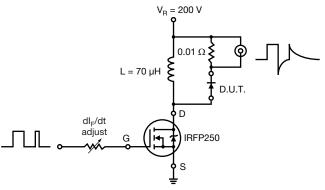
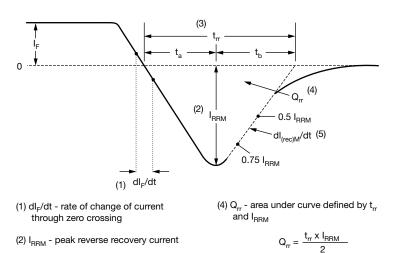


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (3)  $t_{rr}$  reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) dl<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>
- Fig. 10 Reverse Recovery Waveform and Definitions

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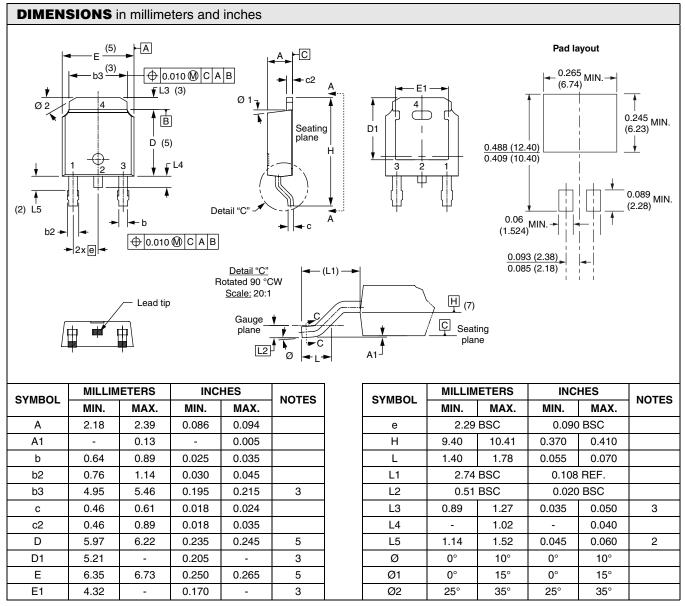
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Device code	VS-	MUR	D	6	20	СТ	TRL	PbF		
		2	3	4	5	6	7	8	I	
	1	- Visł	nay Sen	nicondu	ctors pro	oduct				
	2	- Ultra	afast MI	JR serie	es					
	3	- D=	D-PAK							
	4	- Cur	rent rati	ng (6 =	6 A)					
	5	- Volt	age rati	ng (20 =	= 200 V	) г			]	
	6	- CT :	CT = Center tap (dual) TR = Tape and reel							
	7	- Тар	Tape and reel suffix TRL = Tape and reel (left orie							
	8	- PbF	= Lead	l (Pb)-fr	ee	L				

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95016						
Part marking information	www.vishay.com/doc?95059						
Packaging information	www.vishay.com/doc?95033						



Vishay High Power Products

### D-PAK (TO-252AA)



#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- <sup>(2)</sup> Lead dimension uncontrolled in L5
- <sup>(3)</sup> Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- <sup>(5)</sup> Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(6)</sup> Dimension b1 and c1 applied to base metal only
- <sup>(7)</sup> Datum A and B to be determined at datum plane H
- <sup>(8)</sup> Outline conforms to JEDEC outline TO-252AA

For technical questions concerning discrete products, contact: <u>diodes-tech@vishay.com</u> For technical questions concerning module products, contact: <u>ind-modules@vishay.com</u>



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